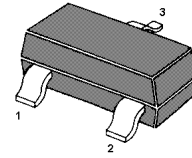


NPN Silicon Epitaxial Planar Transistor

for high frequency amplifier applications
for FM IF, OSC stage and AM CONV. IF stage

The transistor is subdivided into three groups, R, O and Y, according to its DC current gain.



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	50	mA
Base Current	I_B	10	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	-55 to +125	$^\circ\text{C}$

Characteristics at $T_{amb} = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 12\text{ V}$, $I_C = 2\text{ mA}$ Current Gain Group	R	h_{FE}	40	-	80	-
	O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
Collector Cutoff Current at $V_{CB} = 35\text{ V}$	I_{CBO}	-	-	0.1	μA	
Emitter Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	-	0.1	μA	
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	-	0.4	V	
Base Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{BE(sat)}$	-	-	1	V	
Current Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 1\text{ mA}$	f_T	100	-	400	MHz	
Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	2	3.2	pF	
Power Gain at $V_{CE} = 6\text{ V}$, $-I_E = 1\text{ mA}$, $f = 10.7\text{ MHz}$	G_{pe}	27	30	33	dB	

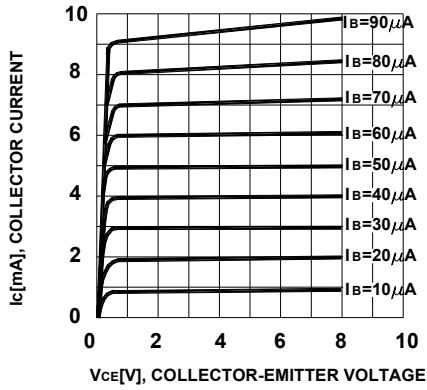


Figure 1. Static Characteristic

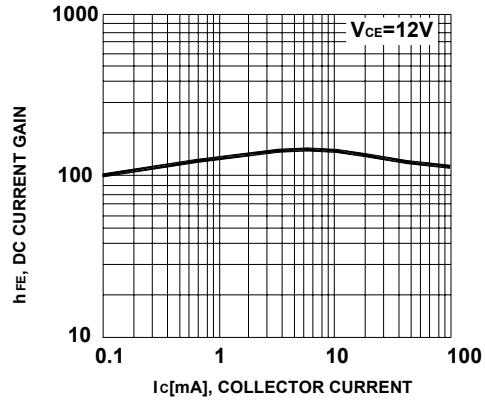


Figure 2. DC Current Gain

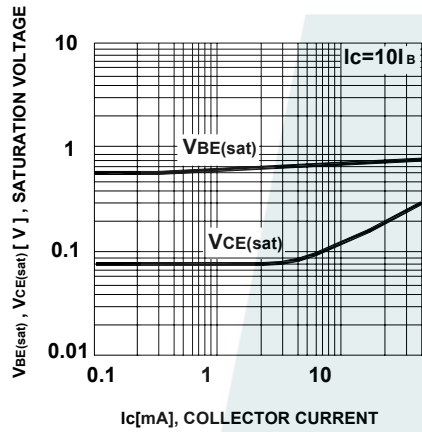


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Satruation Voltage

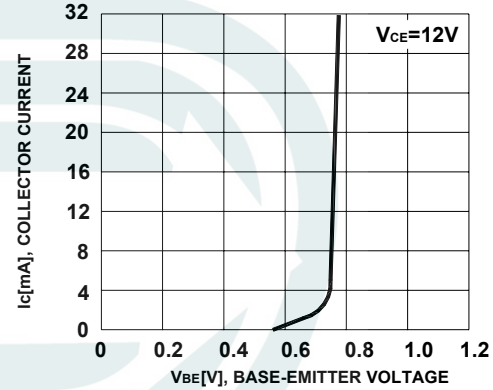


Figure 4. Base-Emitter On Voltage

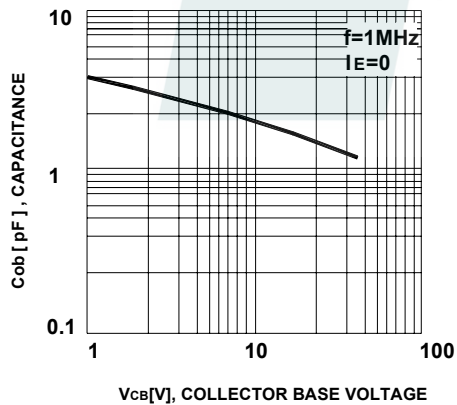


Figure 5. Collector Output Capacitance

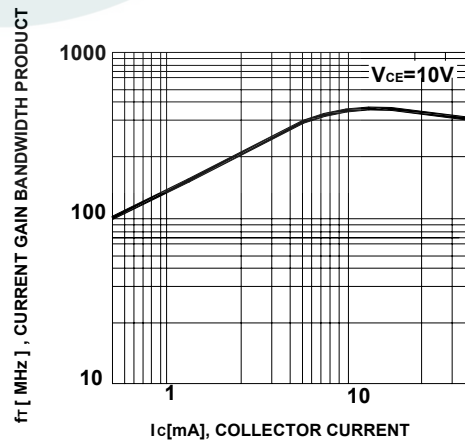


Figure 6. Current Gain Bandwidth Product